

IN THE SPECIFICATION:

Please replace the title beginning on page 1, line 1 with the following:

PROCESS FOR PRODUCING SEMICONDUCTOR DEVICE AND SEMICONDUCTOR
DEVICE A SEMICONDUCTOR DEVICE WITH AN IMPROVED GATE ELECTRODE
PATTERN AND A METHOD OF MANUFACTURING THE SAME

Please replace the paragraph beginning on page 1, line 4 with the following:

This application is a Divisional of U.S. Application Serial No. 09/418,035 filed on October 14, 1999, hereby incorporated by reference as to its entirety. This application is based upon and claims the benefit of priority from the prior Japanese Patent Application 10-293901, filed October 15, 1998, the entire contents of which are incorporated herein by reference. The present invention relates to a gate structure of a semiconductor device and, particularly, to a cell layout of an SRAM (Static Random Access Memory) having a MOS transistor and to a reticle pattern for producing a semiconductor device.